

## Silicon Fast Recovery Diode

$V_{RRM} = 50\text{ V} - 1000\text{ V}$   
 $I_F = 6\text{ A}$

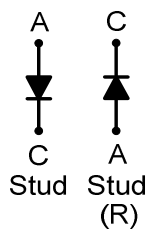
### Features

- High Surge Capability
- Types up to 1000 V  $V_{RRM}$

DO-4 Package

### Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



### Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	FR6J(R)05	FR6K(R)05	FR6M(R)05	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	800	1000	V
RMS reverse voltage	$V_{RMS}$		420	560	700	V
DC blocking voltage	$V_{DC}$		600	800	1000	V
Continuous forward current	$I_F$	$T_C \leq 100\text{ }^\circ\text{C}$	6	6	6	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	135	135	135	A
Operating temperature	$T_j$		-65 to 150	-65 to 150	-65 to 150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$

### Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	FR6J(R)05	FR6K(R)05	FR6M(R)05	Unit
Diode forward voltage	$V_F$	$I_F = 6\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	1.4	1.4	1.4	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	25	25	25	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	6	6	6	mA

### Recovery Time

Parameter	Symbol	Conditions	FR6J(R)05	FR6K(R)05	FR6M(R)05	Unit
Maximum reverse recovery time	$T_{RR}$	$I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{RR} = 0.25\text{ A}$	500	500	500	nS

### Thermal characteristics

Parameter	Symbol	FR6J(R)05	FR6K(R)05	FR6M(R)05	Unit
Thermal resistance, junction - case	$R_{thJC}$	2.5	2.5	2.5	$^\circ\text{C/W}$

